

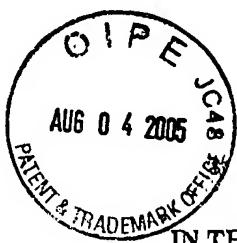
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4002/003



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of:

Chao-Chieh Tsai

Serial No.: 10/623,907

Filed: 07/18/2003

For: HIGH FMAX DEEP SUBMICRON  
MOSFET

Confirmation Number: 5380

Group Art Unit: 2818

Examiner: Luu, Chuong

TKHR Docket: 252016-2380  
Top Team Docket: 0503-5624US

DECLARATION UNDER RULE 132  
Commissioner for Patents  
Washington, D.C. 20231

Sir:

I, Chao-Chieh Tsai hereby declaration that:

1. My name is Chao-Chieh Tsai, and I am a co-inventor of the subject matter claimed in the present application (identified above).
2. I am advised that the U.S. Patent & Trademark Office has rejected the claims of this patent application, based on disclosed teachings in U.S. patent 6,376,351 B1 (hereinafter the '351 patent).
3. I am the inventor of the subject matter claimed in the '351 patent, as well as the inventor of the corresponding subject matter that is disclosed in the '351 patent.
4. I have assigned all right, title, and interest in both the '351 patent and the present application to my employer (Taiwan Semiconductor Manufacturing Company).
5. As such, I do not believe the teachings of the '351 patent should be applied to reject the claims in the present application.

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LOCATION:

RX TIME 08/01 '05 03:38

Serial No.: 10/623,907

I hereby declare: (a) that all statements made herein of my own knowledge are true; (b) that all statements made on information and belief are believed to be true; (c) that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code; and (d) that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Chao-Chieh Tsai  
Chao-Chieh Tsai

07/07/2005  
Date

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